	Application No.	Applicant(s)	Applicant(s)	
Notice of Allowability	10/613,412 KIM, KWANG-TAE			
	Examiner	Art Unit	i	
estatura mendensia dipusus debahan mendentahan menerakan dipusuh dendentahan dendentahan sebagai mengenakan ber	Tu-Tu Ho	2818	An	
The MAILING DATE of this communication apperature All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT R of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED) or other appropriate comi IGHTS This application is	with the correspondence addre	ed	
1. This communication is responsive to Papers filed 07/03/20	<u>003</u> .			
2. The allowed claim(s) is/are <u>1-14</u> .				
3. \square The drawings filed on <u>03 July 2003</u> are accepted by the Ex	kaminer.			
4. ☑ Acknowledgment is made of a claim for foreign priority ur a) ☑ All b) ☐ Some* c) ☐ None of the:	nder 35 U.S.C. § 119(a)-(d) or (f).		
 Certified copies of the priority documents have 	been received.	•		
Certified copies of the priority documents have		ion No.		
3. Copies of the certified copies of the priority do	cuments have been receiv	ed in this national stage applicati	ion from the	
International Bureau (PCT Rule 17.2(a)).		-4 me manerial stage applicat	ormoniale	
* Certified copies not received:		†		
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE. 5. A SUBSTITUTE OATH OR DECLARATION must be submitted the submitted of the submitted particular	ENT of this application. itted. Note the attached EX	(AMINER'S AMENDMENT or NO		
IN ONVIAL PATENT APPLICATION (PTO-152) Which give	es reason(s) why the oath	or declaration is deficient.	OTICE OF	
6. CORRECTED DRAWINGS (as "replacement sheets") mus	t be submitted.	* *		
(a) Including changes required by the Notice of Draftspers	on's Patent Drawing Revie	ew (PTO-948) attached		
1) ☐ hereto or 2) ☐ to Paper No./Mail Date	•	٠.		
(b) ☐ including changes required by the attached Examiner's Paper No./Mail Date	Amendment / Comment of	or in the Office action of		
Identifying indicia such as the application number (see 37 CFR 1. each sheet. Replacement sheet(s) should be labeled as such in the	84(c)) should be written on	the drawings in the front (not the b	pack) of	
 DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT F 	SIT OF BIOLOGICAL MAT	FRIAL must be submitted. No	ote the	
	00	:	•	
	9			
Attachm nt(s) 1. ☑ Notice of References Cited (PTO-892)	- -		-8-	
2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948)		nformal Patent Application (PTO- Summary (PTO-413),	·152) ·	
B. ☐ Information Disclosure Statements (PTO-1449 or PTO/SB/08	Paper No.	/Mail Date : Amendment/Comment	• •	
Paper No./Mail Date Examiner's Comment Regarding Requirement for Deposit	•			
of Biological Material		Statement of Reasons for Allow	rance	
	9. 🗌 Other			
Superviso	avid Nelms pry Patent Examiner logy Center 2800			

Application/Control Number: 10/613,412

Art Unit: 2818

DETAILED ACTION

Priority

1. Receipt is acknowledged of papers submitted under 35 U.S.C. 119(a)-(d), which papers have been placed of record in the file.

Allowable Subject Matter

2. Claims 1-14 are allowable over the prior art of record.

The following is an examiner's statement of reasons for allowance: The prior art of record fails to teach or render obvious a memory device and a method of fabricating thereof having all exclusive limitations as recited in claims 1, 5, and 10, comprising a first transistor, a second transistor, a substrate including active regions, a first conductive layer pattern, an insulating layer, a second conductive layer pattern, a first conductive line, and a second conductive line, wherein each of the first transistor and the second transistor comprises the first conductive layer pattern and the second conductive layer pattern; characterized in that either the first conductive layer pattern of the first transistor is floated (referred to as a floating gate stack in the art) or the first transistor further includes a tunnel insulating layer (referred to as a floating gate stack in the art), that the second conductive layer pattern of the first transistor is connected from a memory cell to an adjacent memory cell and constitutes the first conductive line (referred to as a sense line or word line in the art), that the first conductive layer pattern and the second conductive plugs, and

that either the second transistor constitutes a select transistor or the second conductive pattern of the second transistor is connected to the second conductive line which is also termed a word line.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

- The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Copies of the references are not being furnished with this Office Action per MPEP § 707.05(a).
- a) U.S. Patent 6,316,317 to Kawata et al. discloses a 2-T memory cell where thickness of a first gate insulating layer of the selection transistor is smaller than the thickness of a second gate insulating layer of the memory transistor.
- b) U.S. Patent 6,555,869 to Park discloses a 2-T memory cell where each of the source and drain of each of the transistor has a first doped region and a second doped region.
- 4. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Tu-Tu Ho whose telephone number is (571) 272-1778. The examiner can normally be reached on 6:30 am 5:00 pm.

Art Unit: 2818

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, DAVID NELMS can be reached on (571) 272-1787. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 872-9306 for regular communications and (703) 872-9306 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-1782.

TH

Tu-Tu Ho May 20, 2004 David Nelms
Supervisory Patent Examiner
Technology Center 2800